

## **isc Silicon NPN Power Transistor**

# **BUW39**

#### **DESCRIPTION**

- · High Current Capability
- · Fast Switching Speed
- · Low Saturation Voltage and High Gain
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

Designed for use in high frequency and efficiency converters such as motor controllers and industrial equipment such as:

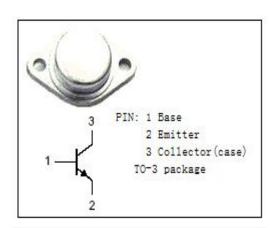
- · Switching regulators
- Motor control
- High frequency and efficiency converters

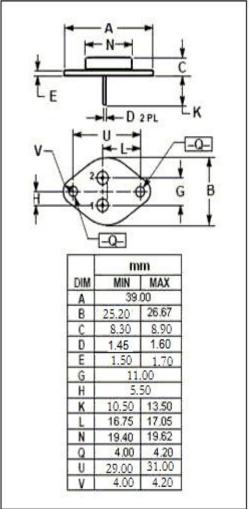
### Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	160	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7	V	
Ic	Collector Current-Continuous	30	Α	
I <sub>CM</sub>	Collector Current-Peak	40	Α	
lв	Base Current-Continuous	6	Α	
I <sub>BM</sub>	Base Current-peak	15	Α	
Pc	Collector Power Dissipation @Tc=25℃	150	W	
Tj	Junction Temperature	200	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-65~200	$^{\circ}$	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.17	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	80			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 50mA; I <sub>C</sub> = 0	7			V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	Ic= 15A; I <sub>B</sub> = 1.5A			0.5	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	Ic= 30A; I <sub>B</sub> = 3A			1.2	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 30A; I <sub>B</sub> = 3A			2.0	V
I <sub>CEX</sub>	Collector Cutoff Current	$V_{CE} = V_{CEX}; V_{BE} = -1.5V$ $V_{CE} = V_{CEX}; V_{BE} = -1.5V; T_{C} = 100 ^{\circ}C$			1.0 3.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V	40			

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